

Germanium Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.					Characteristics									SPECIAL FEATURES
									h _{FE}			f _T		V _{CE(SAT)}				
				V _{CB} V	V _{CE} V	V _{EB} V	I _C A	P _{tot} W	I _C A	Min.	Max.	I _C A	Min. Mc/s	I _C A	I _B A	Max. V		
PNP Medium Power	2N524	TO5	A	-45	-30	-15	0.5	0.225	0.1	23	—	0.001	0.8	—	0.002	0.13		
	2N525	TO5	A	-45	-30	-15	0.5	0.225	0.1	30	—	0.001	1.0	—	0.002	0.13		
	2N526	TO5	A	-45	-30	-15	0.5	0.225	0.1	47	—	0.001	1.3	—	0.002	0.13		
	2N527	TO5	A	-45	-30	-15	0.5	0.225	0.1	65	—	0.001	1.5	—	0.002	0.03		
	2N1141		DM	-35	—	-1.0	0.1	0.75	0.01	10	—	0.01	400	0.05	0.01	2		
	2N1142		DM	-30	—	-0.7	0.1	0.75	0.01	10	—	0.01	310	0.05	0.01	2		
	2N1143		DM	-25	—	-0.5	0.1	0.75	0.01	10	—	0.01	250	0.05	0.01	2		
PNP High Power	2N456A	TO3	A	-40	-40	-20	7	150†	-5	30	90	-1	10.43	-5	-0.5	-0.5	≡ 2G220 ≡ 2G221 ≡ 2G222 ≡ 2G223 ≡ 2G224 ≡ 2G225 ≡ 2G226 ≡ 2G227 ≡ 2G228 ≡ 2G229 ≡ 2G230 ≡ 2G231	
	2N457A	TO3	A	-60	-60	-20	7	150†	-5	30	90	-1	10.43	-5	-0.5	-0.5		
	2N458A	TO3	A	-80	-80	-20	7	150†	-5	30	90	-1	10.43	-5	-0.5	-0.5		
	2N511	MD4	A	-40	-40	-30	10	80†	-10	10	—	-1	10.26	-10	-1.5	-0.5		
	2N511A	MD4	A	-60	-60	-30	10	80†	-10	10	—	-1	10.26	-10	-1.5	-0.5		
	2N511B	MD4	A	-80	-80	-30	10	80†	-10	10	—	-1	10.26	-10	-1.5	-0.5		
	2N512	MD4	A	-40	-40	-30	15	80†	-15	10	—	-1	10.28	-15	-2.25	-0.75		
	2N512A	MD4	A	-60	-60	-30	15	80†	-15	10	—	-1	10.28	-15	-2.25	-0.75		
	2N512B	MD4	A	-80	-80	-30	15	80†	-15	10	—	-1	10.28	-15	-2.25	-0.75		
	2N513	MD4	A	-40	-40	-30	20	80†	-20	10	—	-1	10.3	-20	-3.0	-1.25		
	2N513A	MD4	A	-60	-60	-30	20	80†	-20	10	—	-1	10.3	-20	-3.0	-1.25		
	2N513B	MD4	A	-80	-80	-30	20	80†	-20	10	—	-1	10.3	-20	-3.0	-1.25		
	2N514	MD4	A	-40	-40	-30	25	80†	-25	10	—	-1	10.43	-25	-3.75	-1.25		
	2N514A	MD4	A	-60	-60	-30	25	80†	-25	10	—	-1	10.43	-25	-3.75	-1.25		
	2N514B	MD4	A	-80	-80	-30	25	80†	-25	10	—	-1	10.43	-25	-3.75	-1.25		
	2N1021	TO3	A	-100	-100	-20	7	150†	-5	30	90	-1	10.43	-5	-0.5	-0.5		
	2N1022	TO3	A	-120	-120	-20	7	150†	-5	30	90	-1	10.43	-5	-0.5	-0.5		
	2N1046	TO3	AD	-100	-50	-20	20	50†	-5	60	200	0.5A	20	-5	-0.5	-0.4		
	2N1907	TO3	AD	-100	-100	-1.5	20	150†	-15	10	—	-1	20	-15	-1.5	-1.0		
	2N1908	TO3	AD	-130	-130	-1.5	20	150†	-15	10	—	-1	20	-15	-1.5	-1.0		
	TI3027	TO3	A	-45	-40	-20	7	150†	-3	40	250	-1	0.2	-3	-0.3	-0.5		
	TI3028	TO3	A	-60	-50	-20	7	150†	-3	40	250	-1	0.2	-3	-0.3	-0.5		
	TI3029	TO3	A	-30	-55	-20	7	150†	-3	40	250	-1	0.2	-3	-0.3	-0.5		
	TI3030	TO3	A	-100	-60	-20	7	150†	-3	40	250	-1	0.2	-3	-0.3	-0.5		
	TI3031	TO3	A	-120	-65	-20	7	150†	-3	40	250	-1	0.2	-3	-0.3	-0.5		

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":	Under h _{FE} :	Under f _T :	Under Dissipation:
A — Alloyed	* — h _{FE}	φ — f _{hfb}	† — dissipation at T _{case} = 25°C
D — Diffused		Δ — f _{hfe}	
E — Epitaxial		‡ — typical	
G — Grown			
M — Mesa			
P — Planar			

The transistor types tabulated in pp 7-17 form the Texas Instruments Limited Preferred and Guidance list for new designs. In addition, the types listed overleaf are readily available. Omission of a type from the Preferred list does not imply that a limit has been set to the production life.